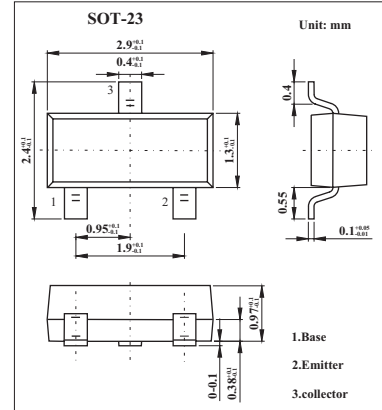


PNP Silicon AF Transistors
BC808



■ Features

- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_c	-800	mA
power dissipation	P_D	310	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V_{CBO}	$I_c = -10 \mu\text{A}, V_{BE} = 0$	-30			V
Collector-to-emitter breakdown voltage	V_{CEO}	$I_c = -10 \text{mA}, I_B = 0$	-25			V
Emitter-to-base breakdown voltage	V_{EBO}	$I_E = -10 \mu\text{A}, I_c = 0$	-5			V
Collector cutoff current	I_{CES}	$V_{CB} = -25 \text{V}, V_{BE} = 0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4 \text{V}, I_c = 0$			-100	nA
DC current gain *	h_{FE}	$I_c = -100 \text{mA}, V_{CE} = -1 \text{V}$	100		630	
		$I_c = -300 \text{mA}, V_{CE} = -1 \text{V}$	60			
Collector saturation voltage *	$V_{CE(sat)}$	$I_c = -500 \text{mA}, I_B = -50 \text{mA}$			-0.7	V
Base emitter on voltage	$V_{BE(on)}$	$V_{CE} = -1 \text{V}, I_c = 300 \text{mA}$			-1.2	V
Output Capacitance	C_{ob}	$V_{CB} = -10 \text{V}, f = 1 \text{MHz}$			12	pF
Transition frequency	f_T	$I_c = -10 \text{mA}, V_{CE} = -5 \text{V}, f = 50 \text{MHz}$		100		MHz

* Pulsed: $PW \leq 350 \mu\text{s}$, duty cycle $\leq 2\%$

■ Marking

NO.	BC808-16	BC808-25	BC808-40
Marking	9GA	9GB	9GC
h_{FE}	100 ~ 250	160 ~ 400	250 ~ 630